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LM136A-2.5QML 2.5V Reference Diode

Check for Samples: LM136A-2.5QML

FEATURES

- Available with Radiation Specification
 - Total Ionizing Dose 100 krad(Si)
 - ELDRS Free 100 krad(Si)
- Low Temperature Coefficient
- Wide Operating Current of 400 µA to 10 mA .
- **Specified Temperature Stability**
- **Easily Trimmed for Minimum Temperature Drift**
- Fast Turn-on
- 3-Lead Transistor Package

DESCRIPTION

The LM136A-2.5QML integrated circuit is a precision 2.5V shunt regulator diode. This monolithic IC voltage reference operates as a low-temperature-coefficient 2.5V zener with 0.2Ω dynamic impedance. A third terminal on the LM136A-2.5QML allows the reference voltage and temperature coefficient to be trimmed easily.

The LM136A-2.5QML is useful as a precision 2.5V low voltage reference for digital voltmeters, power supplies or op amp circuitry. The 2.5V make it convenient to obtain a stable reference from 5V logic Further, since the LM136A-2.5QML supplies. operates as a shunt regulator, it can be used as either a positive or negative voltage reference.

Connection Diagram

Bottom View



Figure 1. TO Package See Package Number NDV0003H



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Schematic Diagram



Typical Applications







[†]Adjust to 2.490V ^{*}Any silicon signal diode







Figure 4. Wide Input Range Reference

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

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STRUMENTS

EXAS

Absolute Maximum Ratings⁽¹⁾

| Reverse Current | 15 mA |
|--|---|
| Forward Current | 10 mA |
| Storage Temperature | -60° C ≤ T _A ≤ +150°C |
| Operating Temperature Range ⁽²⁾ | −55°C ≤ T _A ≤ +125°C |
| Maximum Junction Temperature (| +150°C |
| Lead Temperature (Soldering 10 s | 300°C |
| Thermal Resistance | 354°C/W |
| | 77°C/W |
| | 46°C/W |
| ESD Rating ⁽³⁾ | 1,000V |

(1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is functional, but do not ensure specific performance limits. For ensured specifications and test conditions, see the Electrical Characteristics. The ensured specifications apply only for the test conditions listed. Some performance characteristics may degrade when the device is not operated under the listed test conditions.

(2) The maximum power dissipation must be derated at elevated temperatures and is dictated by T_{Jmax} (maximum junction temperature), θ_{JA} (package junction to ambient thermal resistance), and T_A (ambient temperature). The maximum allowable power dissipation at any temperature is $P_{Dmax} = (T_{Jmax} - T_A)/\theta_{JA}$ or the number given in the Absolute Maximum Ratings, whichever is lower. Human body model, 1.5K Ω in series with 100pF.

(3)

Quality Conformance Inspection

Mil-Std-883, Method 5005 - Group A

| Subgroup | Description | Temp°C |
|----------|---------------------|--------|
| 1 | Static tests at | +25 |
| 2 | Static tests at | +125 |
| 3 | Static tests at | -55 |
| 4 | Dynamic tests at | +25 |
| 5 | Dynamic tests at | +125 |
| 6 | Dynamic tests at | -55 |
| 7 | Functional tests at | +25 |
| 8A | Functional tests at | +125 |
| 8B | Functional tests at | -55 |
| 9 | Switching tests at | +25 |
| 10 | Switching tests at | +125 |
| 11 | Switching tests at | -55 |
| 12 | Settling time at | +25 |
| 13 | Settling time at | +125 |
| 14 | Settling time at | -55 |



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LM136A-2.5QML Electrical Characteristics DC Parameters⁽¹⁾⁽²⁾

The following conditions apply, unless otherwise specified. $I_{R} = 1 \text{ mA}$

| Parameter | | Test Conditions | Notes | Min | Max | Unit | Sub- groups |
|-------------------|---------------------------|--------------------------------|--------------------|-----------|-----------|------|----------------|
| I _{Adj} | Adjust Current | $V_{Adj} = 0.7V$ | | -125 | +125 | μA | 1, 2, 3 |
| ΔV_Z | Delta Zapar Valtaga | 0.4m0.51.510.m0 | | | 6.0 | mV | 1 |
| | Della Zerier voltage | 0.4 mA $\leq 1_Z \leq 10$ mA | | | 10 | mV | 2, 3 |
| Vz | | V _{Adi} = Open | | 2.46 5 | 2.51 5 | V | 1 |
| | | | | 2.44 | 2.54 | V | 2, 3 |
| | Zener Voltage | V 0.7V | | 2.39 | 2.49 | V | 1 |
| | | $v_{Adj} = 0.7 v$ | | 2.29 | 2.49 | V | 2, 3 |
| | | $V_{Adj} = 1.9V$ | | 2.49 | 2.69 | V | 1, 2, 3 |
| 7 | Reverse Dynamia Impedance | | See ⁽³⁾ | | 0.6 | Ω | 1 |
| ∠RD | Reverse Dynamic Impedance | | See ⁽³⁾ | | 1.0 | Ω | 2, 3 |
| V _{Stab} | Temperature Stability | V_Z = Adjusted to 2.490V | | | 18 | mV | 2, 3 |

(1) Pre and post irradiation limits are identical to those listed under DC electrical characteristics. These parts may be dose rate sensitive in a space environment and may demonstrate enhanced low dose rate effect. Radiation end point limits for the noted parameters are specified only for the conditions as specified in Mil-Std-883, Method 1019.

(2) Low dose rate testing has been performed on a wafer-by-wafer basis, per test method 1019 condition D of MIL-STD-883, with no enhanced low dose rate sensitivity (ELDRS) effect.

(3) Parameter tested go-no-go only.

LM136A-2.5QML Electrical Characteristics DC Drift Parameters⁽¹⁾⁽²⁾

Delta calculations are performed on QMLV devices at Group B, Subgroup 5 only.

| | Parameter | Test Conditions | Notes | Min | Max | Unit | Sub- groups |
|----|---------------|-------------------------|-------|-----|-----|------|----------------|
| | | V _{Adj} = Open | | -10 | +10 | mV | 1 |
| Vz | Zener Voltage | $V_{Adj} = 0.7V$ | | -10 | +10 | mV | 1 |
| | | V _{Adj} = 1.9V | | -10 | +10 | mV | 1 |

(1) Pre and post irradiation limits are identical to those listed under DC electrical characteristics. These parts may be dose rate sensitive in a space environment and may demonstrate enhanced low dose rate effect. Radiation end point limits for the noted parameters are specified only for the conditions as specified in Mil-Std-883, Method 1019.

(2) Low dose rate testing has been performed on a wafer-by-wafer basis, per test method 1019 condition D of MIL-STD-883, with no enhanced low dose rate sensitivity (ELDRS) effect.

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Typical Performance Characteristics

Figure 9.

Figure 10.



LM136A-2.5QML

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APPLICATION HINTS

The LM136 voltage reference is much easier to use than ordinary zener diodes. It's low impedance and wide operating current range simplify biasing in almost any circuit. Further, either the breakdown voltage or the temperature coefficient can be adjusted to optimize circuit performance.

Figure 12 shows an LM136 with a 10k potentiometer for adjusting the reverse breakdown voltage. With the addition of R1 the breakdown voltage can be adjusted without affecting the temperature coefficient of the device. The adjustment range is usually sufficient to adjust for both the initial device tolerance and inaccuracies in buffer circuitry.

If minimum temperature coefficient is desired, two diodes can be added in series with the adjustment potentiometer as shown in Figure 13. When the device is adjusted to 2.490V the temperature coefficient is minimized. Almost any silicon signal diode can be used for this purpose such as a 1N914, 1N4148 or a 1N457. For proper temperature compensation the diodes should be in the same thermal environment as the LM136. It is usually sufficient to mount the diodes near the LM136 on the printed circuit board. The absolute resistance of R1 is not critical and any value from 2k to 20k will work.



Figure 12. LM136 With Pot for Adjustment of Breakdown Voltage (Trim Range = ±120 mV typical)





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^{*}L1 60 turns #16 wire on Arnold Core A-254168-2 [†]Efficiency $\approx 80\%$





Figure 15. Precision Power Regulator with Low Temperature Coefficient



Figure 16. 5V Crowbar





*Does not affect temperature coefficient





Figure 18. Adjustable Shunt Regulator



Figure 19. Linear Ohmmeter









Figure 21. Bipolar Output Reference



Figure 22. 2.5V Square Wave Calibrator







Figure 23. 5V Buffered Reference





REVISION HISTORY

| Date Released | Revision | Section | Changes |
|---------------|----------|---|--|
| 07/06/07 | A | New Release, Corporate format | 2 MDS datasheets converted into one corporate datasheet format. MNLM136–2.5–X Rev 0A0 and MNLM136A-2.5–X-RH. The ELDRS Part has also been added. Rev. 0E0 will be archived. |
| 10/16/2010 | В | Data Sheet Title, General Description, Order Information, Electrical Characteristics, Application Hints | Update with current device information and format. Removed all references to the LM136-2.5 Non "A" package NSID no longer offered. Added Die NSID's to data sheet. Revision A will be Archived. |



PACKAGING INFORMATION

| Orderable Device | Status | Package Type | Package | Pins | Package Qty | Eco Plan | Lead/Ball Finish | MSL Peak Temp | Op Temp (°C) | Top-Side Markings | Samples |
|------------------|--------|--------------|---------|------|-------------|----------------------------|------------------|------------------|--------------|-------------------|---------|
| | (1) | | Drawing | | | (2) | | (3) | | (4) | |
| 5962R0050101V9A | ACTIVE | DIESALE | Y | 0 | 40 | Green (RoHS & no Sb/Br) | Call TI | Level-1-NA-UNLIM | -55 to 125 | | Samples |
| 5962R0050101VXA | ACTIVE | то | NDV | 3 | 20 | TBD | POST-PLATE | Level-1-NA-UNLIM | -55 to 125 | R0050101VXA Q | Samples |
| 5962R0050102VXA | ACTIVE | то | NDV | 3 | 20 | TBD | POST-PLATE | Level-1-NA-UNLIM | -55 to 125 | R0050102VXA Q | Samples |
| LM136-2.5 MDR | ACTIVE | DIESALE | Y | 0 | 40 | Green (RoHS & no Sb/Br) | Call TI | Level-1-NA-UNLIM | -55 to 125 | | Samples |
| LM136AH-2.5/883 | ACTIVE | то | NDV | 3 | 20 | TBD | POST-PLATE | Level-1-NA-UNLIM | -55 to 125 | LM136A-2.5 Q | Samples |
| LM136AH-2.5RLQV | ACTIVE | то | NDV | 3 | 20 | TBD | POST-PLATE | Level-1-NA-UNLIM | -55 to 125 | R0050102VXA Q | Samples |
| LM136AH-2.5RQV | ACTIVE | ТО | NDV | 3 | 20 | TBD | POST-PLATE | Level-1-NA-UNLIM | -55 to 125 | R0050101VXA Q | Samples |

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

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Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ Only one of markings shown within the brackets will appear on the physical device.

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OTHER QUALIFIED VERSIONS OF LM136A-2.5QML, LM136A-2.5QML-SP :

• Military: LM136A-2.5QML

Space: LM136A-2.5QML-SP

NOTE: Qualified Version Definitions:

- Military QML certified for Military and Defense Applications
- Space Radiation tolerant, ceramic packaging and qualified for use in Space-based application

MECHANICAL DATA

NDV0003H





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